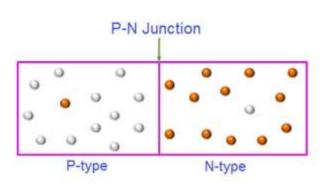
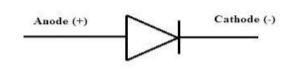
# Electronic Devices

Lecture 4
P-N Junction

Dr. Roaa Mubarak

#### **Diode symbol**





• Diode current voltage Relation :

$$I_D = I_S \left( e^{\frac{V_D}{\eta V_T}} - 1 \right)$$

*V<sub>D</sub>: Voltage across diode* 

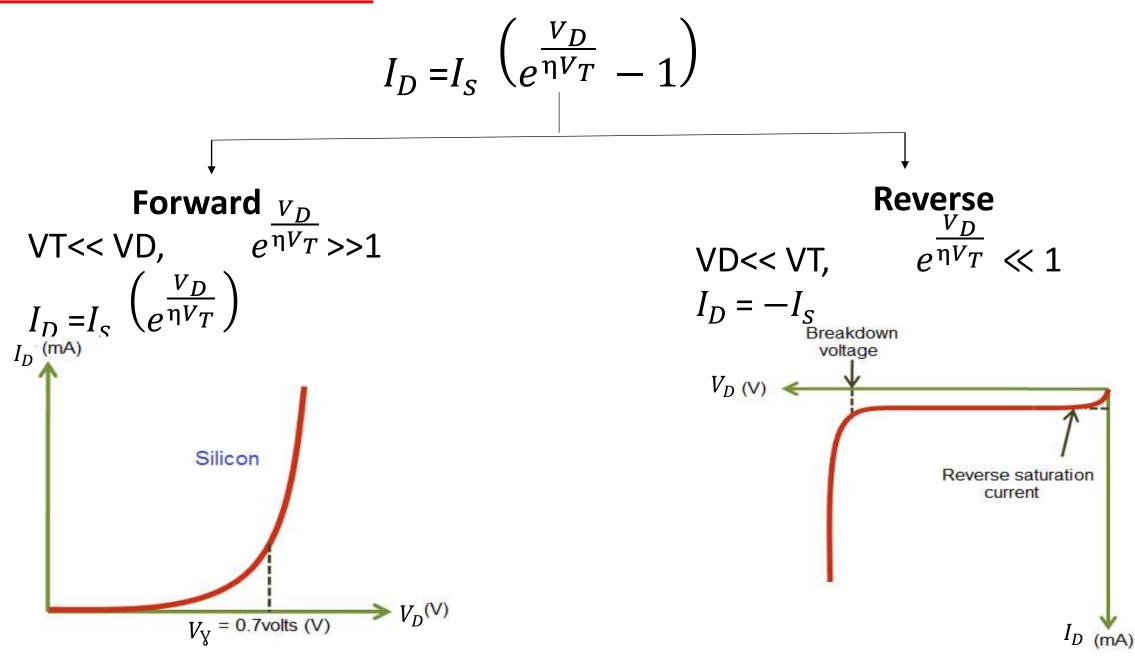
*I<sub>D</sub>* : Diode current

 $I_{S}$ : Reverse sturation current

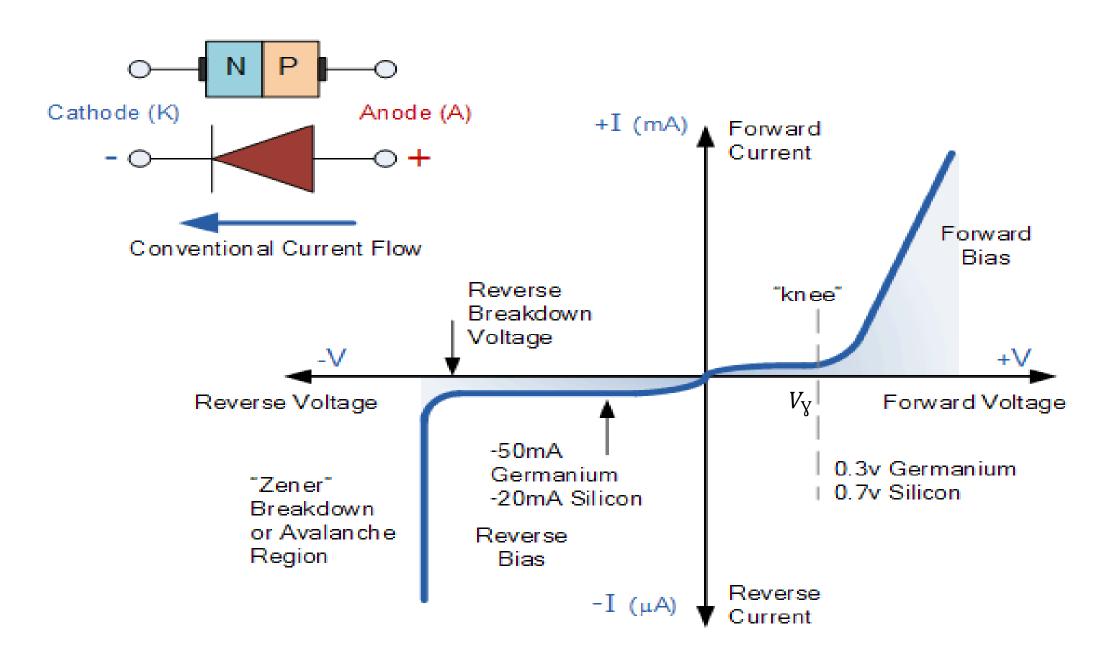
*V<sub>T</sub>: Thermal voltage* 

η: Ideality Factor Constant (Si η=2, Ge η=1)

#### **V-I Characteristics**



#### **V-I Characteristics**



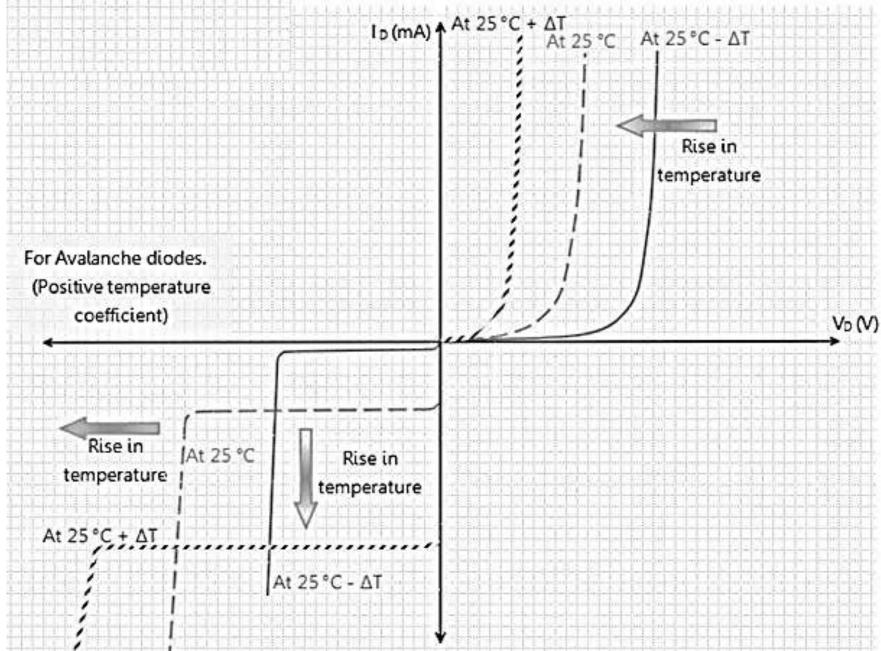
### **Temperature Effects**

- Since  $I_s$ ,  $V_T$  are function of temperature, So diode Char. Also vary with temperature.
- For silicon the charge is approximately 2mv/°C
- The change in  $I_S$  is 7 percent /°C
- The value of  $I_s$  is doubled every 10 °C rise in temperature.

$$I_{s2} = I_{s1} \times 2^{\left(\frac{T_2 - T_1}{10}\right)}$$

Example:  $I_{S1}$ = 1 $\mu$ A ----- then  $I_{S2}$ =  $(1.07)^{10} \approx 2 \mu$ A

## **Temperature Effects**



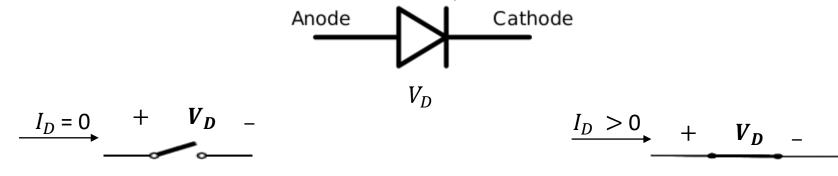
### **Diode Models**

The diode as a circuit elements:

- Ideal Diode Model
- Large Signal model
- Small Signal model

### The Ideal Diode Model

- The diode is designed to allow current to flow in only one direction.
- The perfect diode would be a perfect conductor in one direction (Forward bias) and a perfect insulator in the other direction (reverse bias).  $I_D$



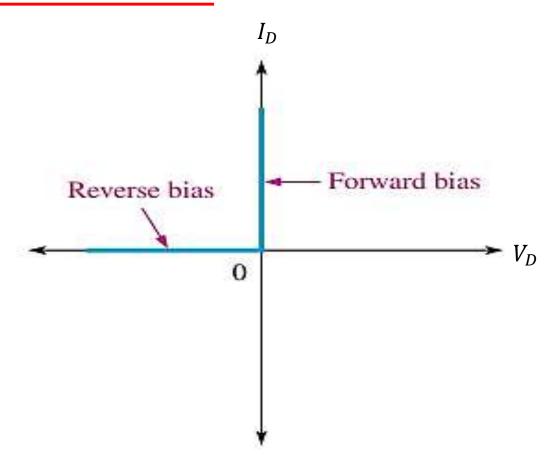
#### **Reverse biased**

$$V_D$$
 < 0 ,  $I_D$  = 0  
Open Circuit

#### Forward biased

$$V_D = 0$$
 ,  $I_D > 0$  Short Circuit ON

### The Ideal Diode Model



Ideal V-I Characteristic Curve (blue)

#### The Ideal Diode Model

#### Example:

Assume the diode in circuit below is ideal.

Determine the value  $I_D$  if:

a) 
$$Vs = 5 V$$
 b)  $Vs = -5V$ 

b) 
$$Vs = -5V$$

#### Sol:

a) With Vs =5V, Diode is forward, for Ideal Model it replaced by short circuit.

$$I_D = \frac{Vs}{R} = \frac{5}{50} = 100mA$$

b) With Vs =-5V, Diode is Reverse, for Ideal Model it replaced by open circuit.

$$I_D = 0$$

